Surface Mount Schottky Power Rectifier

POWERMITE® Power Surface Mount Package

The Schottky Powermite employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop—reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the Powermite has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC–DC and DC–DC converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

Features

- Low Profile Maximum Height of 1.1 mm
- Small Footprint Footprint Area of 8.45 mm2
- Low V_F Provides Higher Efficiency and Extends Battery Life
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- Pb-Free Packages are Available

Mechanical Characteristics

- Powermite is JEDEC Registered as DO-216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 16.3 mg (approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes 260°C Maximum for 10 Seconds



ON Semiconductor®

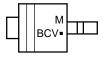
http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 20 VOLTS



POWERMITE CASE 457 PLASTIC

MARKING DIAGRAM



BCV = Device Code

M = Date Code

Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	20	V	
Average Rectified Forward Current (At Rated V _R , T _C = 130°C)	I _O	1.0	А	
Peak Repetitive Forward Current (At Rated V_R , Square Wave, 20 kHz, T_C = 135°C)	I _{FRM}	2.0	А	
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	IFSM	50	А	
Storage Temperature	T _{stg}	-65 to 150	°C	
Operating Junction Temperature	T _J	-65 to 150	°C	
Voltage Rate of Change (Rated V _R , T _J = 25°C)	dv/dt	10,000	V/μs	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance – Junction–to–Lead (Anode) (Note 1) Thermal Resistance – Junction–to–Tab (Cathode) (Note 1) Thermal Resistance – Junction–to–Ambient (Note 1)	R _{tjl} R _{tjtab} R _{tja}	35 23 277	°C/W

^{1.} Mounted with minimum recommended pad size, PC Board FR4, See Figures 9 and 10.

ELECTRICAL CHARACTERISTICS

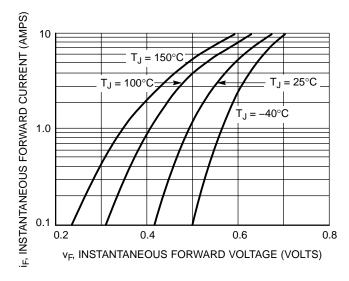
Rating	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 2), See Figure 2	V _F	T _J = 25°C	T _J = 100°C	V
$(I_F = 0.1 \text{ A})$ $(I_F = 1.0 \text{ A})$ $(I_F = 2.0 \text{ A})$		0.455 0.530 0.595	0.360 0.455 0.540	
Maximum Instantaneous Reverse Current (Note 2), See Figure 4	I _R	T _J = 25°C	T _J = 100°C	μΑ
$(V_R = 20 \text{ V})$ $(V_R = 10 \text{ V})$ $(V_R = 5.0 \text{ V})$		10 1.0 0.5	1600 500 300	

^{2.} Pulse Test: Pulse Width \leq 250 $\mu s,$ Duty Cycle \leq 2%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRM120ET1	POWERMITE	
MBRM120ET1G	POWERMITE (Pb-Free)	3000 / Tape & Reel
MBRM120ET3	POWERMITE	
MBRM120ET3G	POWERMITE (Pb-Free)	12,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



1.0 T_J = 150°C

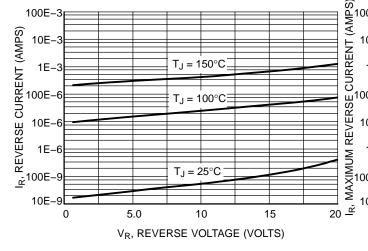
T_J = 150°C

T_J = 25°C

V_F, MAXIMUM INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



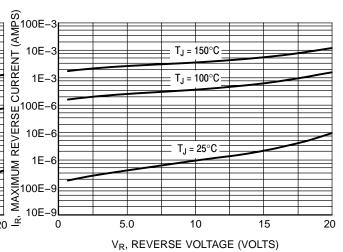
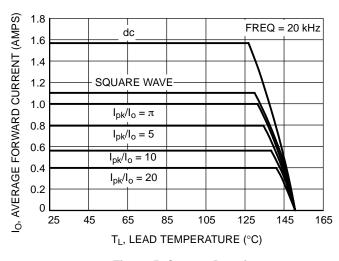


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current



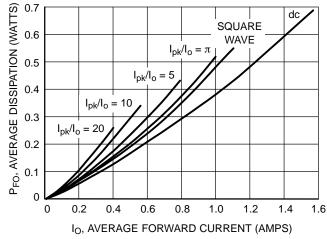


Figure 5. Current Derating

Figure 6. Forward Power Dissipation

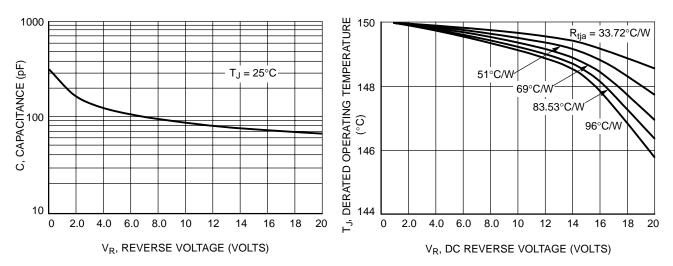


Figure 7. Capacitance

Figure 8. Typical Operating Temperature Derating*

r(t) = thermal impedance under given conditions,

Pf = forward power dissipation, and

Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under \dot{DC} conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

^{*} Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

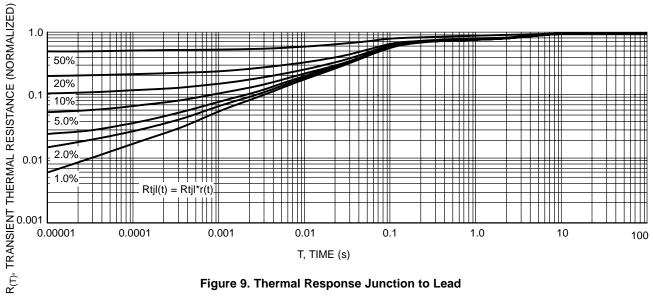


Figure 9. Thermal Response Junction to Lead

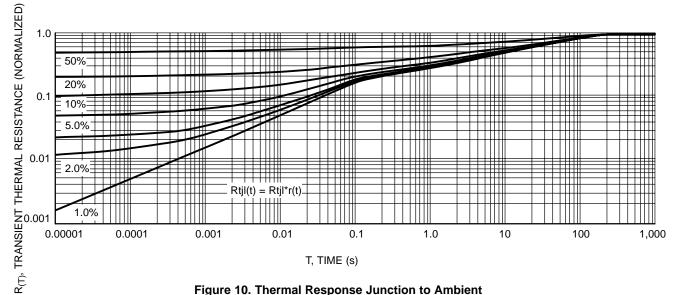
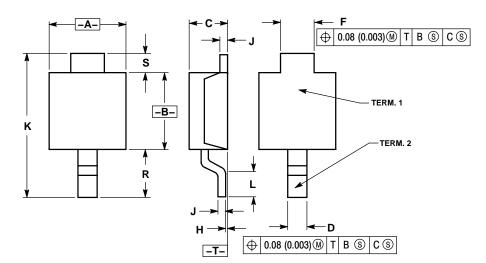


Figure 10. Thermal Response Junction to Ambient

PACKAGE DIMENSIONS

POWERMITE

PLASTIC PACKAGE CASE 457-04 ISSUE D

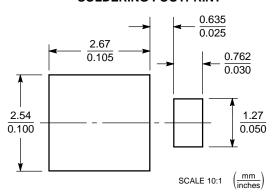


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.75	2.05	0.069	0.081
В	1.75	2.18	0.069	0.086
С	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
Н	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50 REF		0.019 REF	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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